Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V _S	0V to +6V
V _{IN} V _S - 0.5V to	$+V_{S} + 0.5V$

Operating Conditions

Supply Voltage Range	2.5 to 5.5V
Operating Temperature Range	40°C to 85°C
Junction Temperature	150°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10s)	260°C

Package Thermal Resistance

θ _{JA} (SOIC-8)	150°C/W
θ _{JA} (MSOP-8)	200°C/W
θ _{JA} (TSOT23-5)	215°C/W
θ _{JA} (TSOT23-6)	192°C/W
Package thermal resistance (θ_{JA}), JEDEC standard, m test boards, still air.	nulti-layer

ESD Protection

SOIC-8 (HBM)	2.5kV
ESD Rating for HBM (Human Device Model).	Body Model) and CDM (Charged

Electrical Characteristics at +2.7V

 T_A = 25°C, V_S = +2.7V, R_f = 2k Ω , R_L = 2k Ω to $V_S/2;$ G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product			86		MHz
UGBW	Unity Gain Bandwidth(1)	$G = +1, V_{OUT} = 0.05V_{pp}$		215		MHz
BW _{SS}	-3dB Bandwidth	$G = +2, V_{OUT} = 0.2V_{pp}$		85		MHz
BW _{LS}	Large Signal Bandwidth	$G = +2$, $V_{OUT} = 2V_{pp}$		36		MHz
Time Doma	ain		<u> </u>			
t _R , t _F	Rise and Fall Time (1)	V _{OUT} = 0.2V step; (10% to 90%)		3.7		ns
t _S	Settling Time to 0.1%	V _{OUT} = 1V step		40		ns
OS	Overshoot	V _{OUT} = 0.2V step		9		%
SR	Slew Rate	G = -1, 2.7V step		130		V/µs
Distortion/N	Noise Response					
HD2	2nd Harmonic Distortion (1)	5MHz, V _{OUT} = 1V _{pp}		79		dBc
HD3	3rd Harmonic Distortion (1)	5MHz, V _{OUT} = 1V _{pp}		82		dBc
THD	Total Harmonic Distortion (1)	5MHz, V _{OUT} = 1V _{pp}		77		dB
e _n	Input Voltage Noise	>1MHz		16		nV/√Hz
i _n	Input Current Noise	>1MHz		1.3		pA/√Hz
X _{TALK}	Crosstalk ⁽¹⁾	CLC2005, 10MHz		65		dB
DC Perform		CLOCOO, TOWN IZ				
V _{IO}	Input Offset Voltage			-1.6		mV
d _{VIO}	Average Drift			10		μV/°C
I _B	Input Bias Current			3		μΑ
dl _B	Average Drift			7		nA/°C
	Input Offset Current			0.1		μΑ
I _{OS} PSRR	Power Supply Rejection Ratio	DC	52	57		dΒ
	Open Loop Gain	50	32	75		dB
A _{OL}	Supply Current			3.9		mA
ls Disable Ch				3.9		IIIA
	aracteristics (CLC1015) Turn On Time			150		
T _{ON}	Turn Off Time			150 25		ns
T _{OFF}		FMU= D 1000				ns
OFF _{ISO}	Off Isolation	$5MHz$, $R_L = 100Ω$ \overline{DIS} tied to GND		75	100	dB
I _{SD}	Disable Supply Current	DIS tied to GND		58	100	μΑ
Input Chara				4.0		MO
R _{IN}	Input Resistance			4.3		ΜΩ
CIN	Input Capacitance			1.8		pF
CMIR	Common Mode Input Range			-0.3 to 1.5		V
CMRR	Common Mode Rejection Ratio	DC, $V_{CM} = 0$ to $V_S - 1.5V$		87		dB
Output Cha	aracteristics			0.000 +-		I
		$R_L = 10k\Omega$ to $V_S/2$		0.023 to 2.66		V
V_{OUT}	Output Swing	$R_L = 2k\Omega$ to $V_S/2$		0.025 to		V
•001	Catput Swing	11[- 2K12 to Vg / 2		2.653		V
		$R_L = 150\Omega$ to $V_S / 2$		0.065 to 2.55		V
	Output Course			±55		mA
I _{OUT}	Output Current	-40°C to +85°C		±50		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S/2$		±85		mA
V _S	Power Supply Operating Range		2.5	2.7	5.5	V
	1171 0 0			1		1

Notes

^{1.} R_f = $1k\Omega$ was used for optimal performance. (For G = +1, R_f = 0)

Electrical Characteristics at +5V

 T_A = 25°C, V_S = +5V, R_f = 2k Ω , R_L = 2k Ω to $V_S/2;$ G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency [Frequency Domain Response					
GBWP	-3dB Gain Bandwidth Product			90		MHz
UGBW	Unity Gain Bandwidth(1)	$G = +1, V_{OUT} = 0.05V_{pp}$		260		MHz
BW _{SS}	-3dB Bandwidth	$G = +2, V_{OUT} = 0.2V_{pp}$		90		MHz
BW _{LS}	Large Signal Bandwidth	$G = +2$, $V_{OUT} = 2V_{pp}$		40		MHz
Time Doma	in					
t _R , t _F	Rise and Fall Time (1)	V _{OUT} = 0.2V step		3.6		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		40		ns
OS	Overshoot	V _{OUT} = 0.2V step		7		%
SR	Slew Rate	G = -1, 5V step		145		V/µs
Distortion/N	oise Response			•		
HD2	2nd Harmonic Distortion (1)	5MHz, V _{OUT} = 2V _{pp}		71		dBc
HD3	3rd Harmonic Distortion (1)	5MHz, V _{OUT} = 2V _{pp}		78		dBc
THD	Total Harmonic Distortion (1)	5MHz, $V_{OUT} = 2V_{pp}$		70		dB
	D:# :: 1 0 :	NTSC (3.85MHz), AC-Coupled, $R_L = 150\Omega$		0.06		%
DG	Differential Gain	NTSC (3.85MHz), DC-Coupled, $R_L = 150\Omega$		0.08		%
	5:4	NTSC (3.85MHz), AC-Coupled, $R_L = 150\Omega$		0.07		0
DP	Differential Phase	NTSC (3.85MHz), DC-Coupled, $R_L = 150\Omega$		0.06		0
e _n	Input Voltage Noise	>1MHz		16		nV/√Hz
i _n	Input Current Noise	>1MHz		1.3		pA/√Hz
X _{TALK}	Crosstalk ⁽¹⁾	CLC2005, 10MHz		62		dB
DC Perform	ance					
V _{IO}	Input Offset Voltage		-8	1.4	8	mV
d _{VIO}	Average Drift			10		μV/°C
I _B	Input Bias Current		-8	3	8	μΑ
dl _B	Average Drift			7		nA/°C
I _{OS}	Input Offset Current		-0.8	0.1	0.8	μΑ
PSRR	Power Supply Rejection Ratio	DC	52	57		dB
A _{OL}	Open Loop Gain		68	78		dB
I _S	Supply Current			4.2	5.2	mA
Disable Cha	aracteristics (CLC1015)		·			
T _{ON}	Turn On Time			150		ns
T _{OFF}	Turn Off Time			25		ns
OFF _{ISO}	Off Isolation	5MHz, $R_L = 100\Omega$		75		dB
I _{SD}	Disable Supply Current	DIS tied to GND		127	170	μΑ
Input Chara	cteristics					
R _{IN}	Input Resistance			4.3		ΜΩ
C _{IN}	Input Capacitance			1.8		pF
CMIR	Common Mode Input Range			-0.3 to 3.8		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0 to V _S - 1.5V	72	87		dB

Electrical Characteristics at +5V Continued

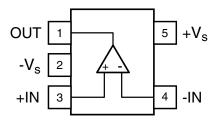
 T_A = 25°C, V_S = +5V, R_f = 2k Ω , R_L = 2k Ω to $V_S/2;$ G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Output Char	acteristics					
		$R_L = 10k\Omega$ to $V_S/2$		0.027 to 4.97		V
V _{OUT}	V _{OUT} Output Swing	$R_L = 2k\Omega$ to $V_S/2$		0.036 to 4.953		V
	$R_L = 150\Omega$ to $V_S/2$	0.3	0.12 to 4.8	4.625	V	
	Output Current			±55		mA
IOUT	I _{OUT} Output Current	-40°C to +85°C		±50		mA
I _{SC}	Short Circuit Current	V _{OUT} = V _S / 2		±85		mA
Vs	Power Supply Operating Range		2.5	5	5.5	V

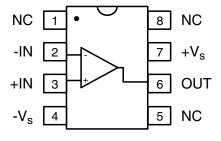
Notes:

^{1.} $R_f = 1k\Omega$ was used for optimal performance. (For G = +1, $R_f = 0$)

CLC1005 Pin ConfigurationsTSOT-5



SOIC-8



CLC1005 Pin Assignments

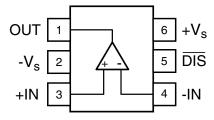
TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-V _S	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V _S	Positive supply

SOIC-8

Pin No.	Pin Name	Description
1	NC	No Connect
2	-IN	Negative input
3	+IN	Positive input
4	-V _S	Negative supply
5	NC	No Connect
6	OUT	Output
7	+V _S	Positive supply
8	NC	No Connect

CLC1015 Pin Configurations TSOT-6

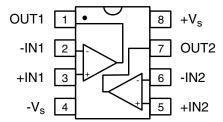


CLC1015 Pin Assignments

TSOT-6

Pin No.	Pin Name	Description
1	OUT	Output
2	-V _S	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	DIS	Disable pin. Enabled if pin is left open or tied to $+V_S$, disabled if pin is tied to $+V_S$ (which is GND in a single supply application.)
6	+V _S	Positive supply

CLC2005 Pin Configuration SOIC-8 / MSOP-8



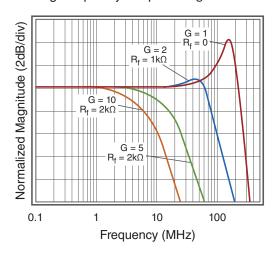
CLC2005 Pin Assignments

SOIC-8 / MSOP-8

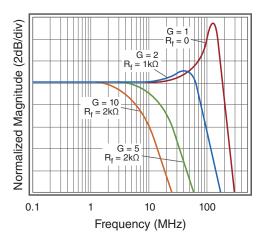
Pin No.	Pin Name	Description	
1	OUT1	Output, channel 1	
2	-IN1	Negative input, channel 1	
3	+IN1	Positive input, channel 1	
4	-V _S	Negative supply	
5	+IN2	Positive input, channel 2	
6	-IN2	Negative input, channel 2	
7	OUT2	Output, channel 2	
8	+V _S	Positive supply	

 T_A = 25°C, V_S = +5V, R_L = 2k Ω to V_S /2, G = +2, R_F = 2k Ω ; unless otherwise noted.

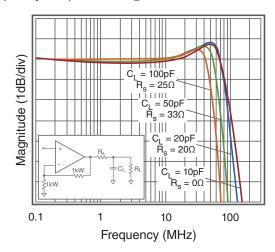
Non-Inverting Frequency Response $V_S = +5V$



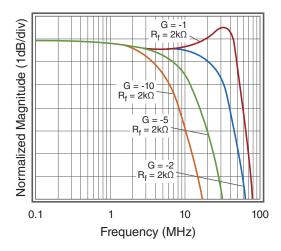
Non-Inverting Frequency Response $V_S = +2.7V$



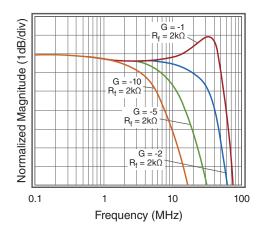
Frequency Response vs CL



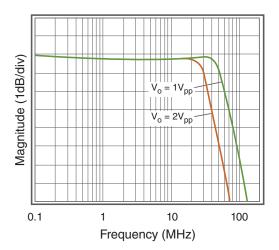
Inverting Frequency Response $V_S = +5V$



Inverting Frequency Response $V_S = +2.7V$

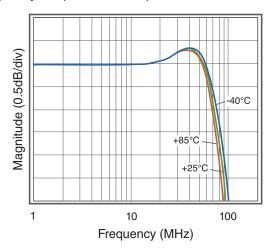


Large Signal Frequency Response

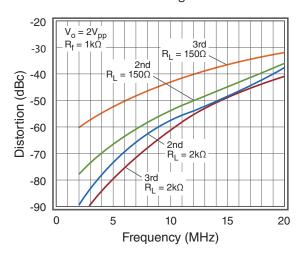


 T_A = 25°C, V_S = +5V, R_L = 2k Ω to V_S /2, G = +2, R_F = 2k Ω ; unless otherwise noted.

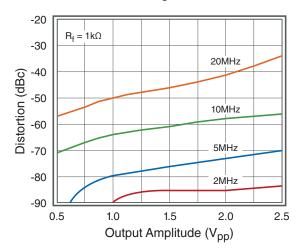
Frequency Response vs. Temperature



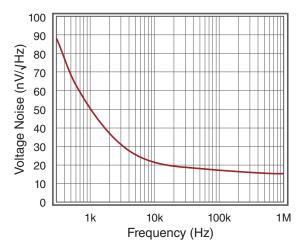
2nd & 3rd Harmonic Distortion $V_S = +5V$



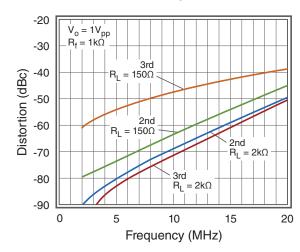
2nd Harmonic Distortion vs VO



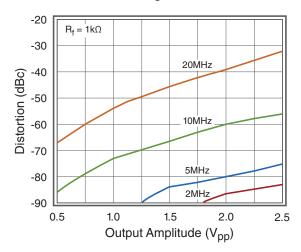
Input Voltage Noise vs Frequency



2nd & 3rd Harmonic Distortion $V_S = +2.7V$

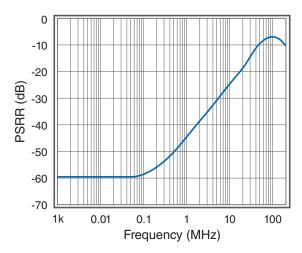


3rd Harmonic Distortion vs V_O

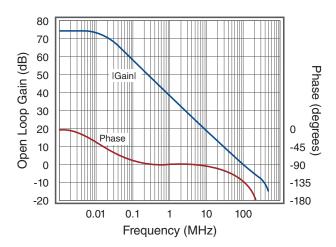


 $T_A = 25$ °C, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 2k\Omega$; unless otherwise noted.

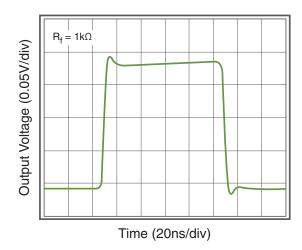
PSRR



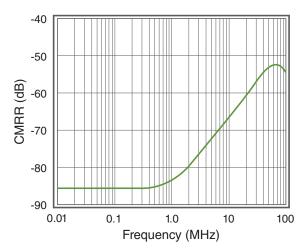
Open Loop Gain & Phase vs. Frequency



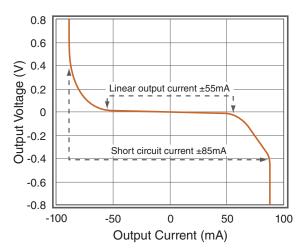
Small Signal Pulse Response V_S = +5V



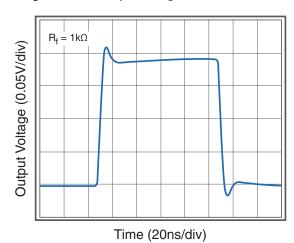
CMRR



Output Current

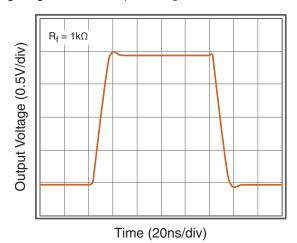


Small Signal Pulse Response V_S = +2.7V

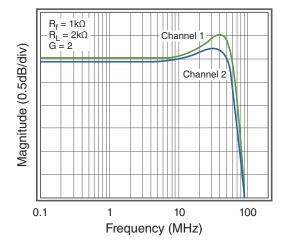


 $T_A = 25$ °C, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 2k\Omega$; unless otherwise noted.

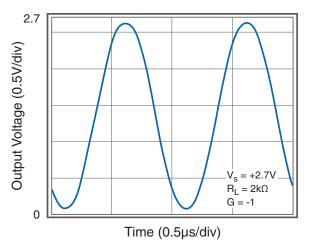
Large Signal Pulse Response $V_S = +5V$



Channel Matching $V_S = +5V$



Output Swing



Application Information

General Description

The CLC1005, CLC1015, and CLC2005 are single supply, general purpose, voltage-feedback amplifiers fabricated on a complementary bipolar process using a patented topography. They feature a rail-to-rail output stage and are unity gain stable. Both gain bandwidth and slew rate are insensitive to temperature.

The common mode input range extends to 300mV below ground and to 1.2V below $V_{\rm S}$. Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition.

The design is short circuit protected and offers "soft" saturation protection that improves recovery time.

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

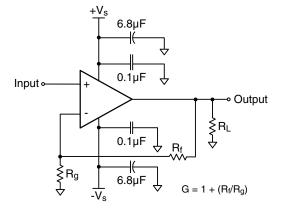


Figure 1: Typical Non-Inverting Gain Circuit

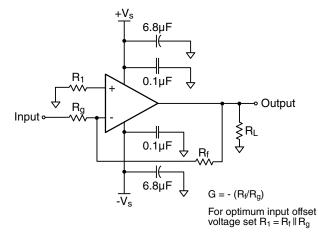


Figure 2: Typical Inverting Gain Circuit

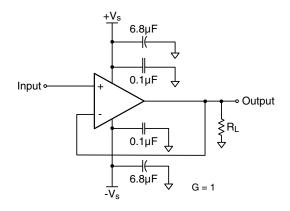


Figure 3: Unity Gain Circuit

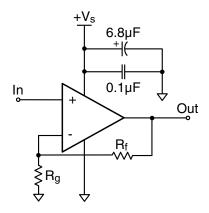


Figure 4: Single Supply Non-Inverting Gain Circuit

At non-inverting gains other than G = +1, keep R_g below $1k\Omega$ to minimize peaking; thus for optimum response at a gain of +2, a feedback resistor of $1k\Omega$ is recommended. Figure 5 illustrates the CLC1005, CLC1015 and CLC2005 frequency response with both $1k\Omega$ and $2k\Omega$ feedback resistors.

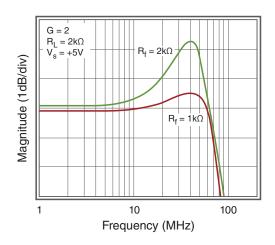


Figure 5: Frequency Response vs. Rf

Overdrive Recovery

For an amplifier, an overdrive condition occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The CLC1005, CLC1015, and CLC2005 will typically recover in less than 20ns from an overdrive condition. Figure 6 shows the CLC2005 in an overdriven condition.

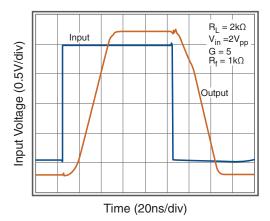


Figure 6: Overdrive Recovery

Enable/Disable Function

The CLC1015 offers an active-low disable pin that can be used to lower its supply current. Leave the pin floating to enable to part. Pull the disable pin to the negative supply (which is ground in a single supply application) to disable the output. During the disable condition, the nominal supply current will drop below $127\mu A$ and the output will be at a high impedance with about 2pF capacitance.

Power Dissipation

Power dissipation should not be a factor when operating under the stated $2k\Omega$ load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 150°C. To calculate the junction temperature, the package thermal resistance value Theta_JA (θ_{JA}) is used along with the total die power dissipation.

$$T_{Junction} = T_{Ambient} + (\theta_{JA} \times P_D)$$

Where $T_{\mbox{\scriptsize Ambient}}$ is the temperature of the working environment.

In order to determine PD, the power dissipated in the load

needs to be subtracted from the total power delivered by the supplies.

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMSsupply}}$$
$$V_{\text{supply}} = V_{\text{S+}} - V_{\text{S-}}$$

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{load})_{BMS^2})/Rload_{eff}$$

The effective load resistor (Rload_{eff}) will need to include the effect of the feedback network. For instance,

Rloadeff in Figure 3 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, P_D can be found from

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(V_{load})_{RMS} = V_{peak} / \sqrt{2}$$

 $(I_{load})_{RMS} = (V_{load})_{RMS} / Rload_{eff}$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{Dvnamic} = (V_{S+} - V_{load})_{RMS} \times (I_{load})_{RMS}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

The CLC1015 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+150°C) is not exceeded under all conditions. Figure 7 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

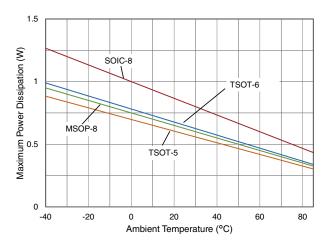


Figure 7. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R_S , between the amplifier and the load to help improve stability and settling performance. Refer to Figure 8.

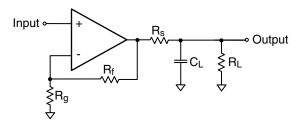


Figure 8. Addition of R_S for Driving Capacitive Loads

Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in approximately <1dB peaking in the frequency response.

C _L (pF)	R _S (Ω)	-3dB BW (MHz)
22pF	0	118
47pF	15	112
100pF	15	91
492pF	6.5	59

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Resurgent has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8μF and 0.1μF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board #	Products
CEB002	CLC1005 and CLC1015 in TSOT
CEB003	CLC1005 in SOIC
CEB006	CLC2005 in SOIC
CEB010	CLC2005 in MSOP

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 9-18. These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -V_S to ground.
- Use C3 and C4, if the -V_S pin of the amplifier is not directly connected to the ground plane.

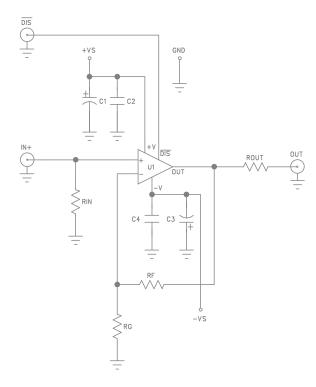


Figure 9. CEB002 and CEB003 Schematic

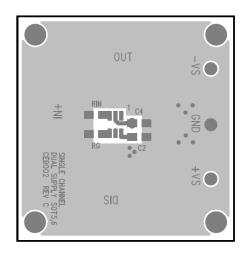


Figure 10. CEB002 Top View

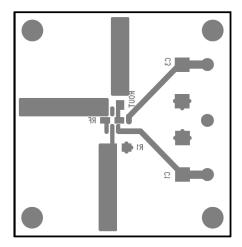


Figure 11. CEB002 Bottom View

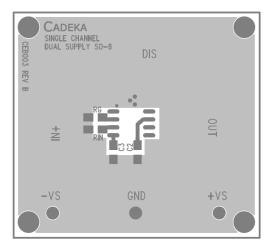


Figure 12. CEB003 Top View

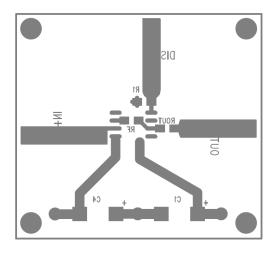


Figure 13. CEB003 Bottom View

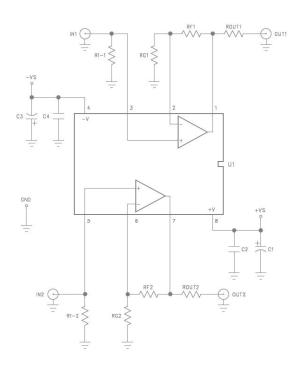


Figure 14. CEB006 & CEB010 Schematic

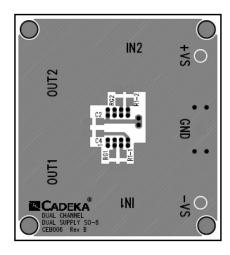


Figure 15. CEB006 Top View

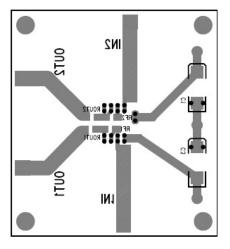


Figure 16. CEB006 Bottom View

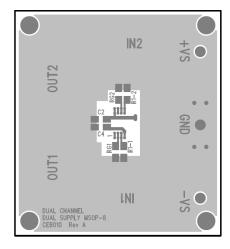


Figure 17. CEB010 Top View

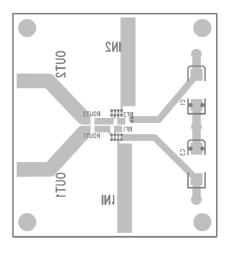
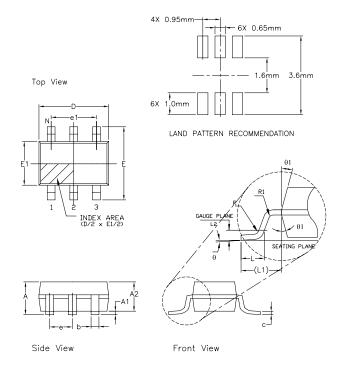


Figure 18. CEB010 Bottom View

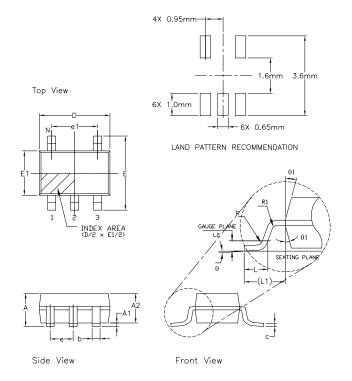
Mechanical Dimensions

TSOT-6 Package



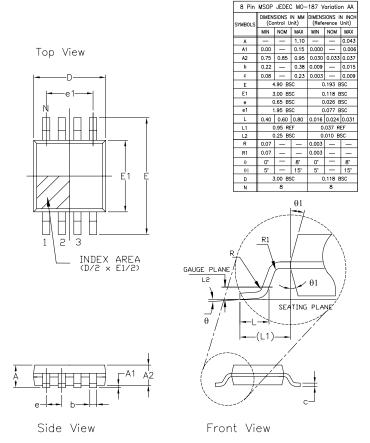
6 PIN TSOT (OPTION 2)						
SYMBOLS	DIMENSION IN MM (Control Unit)			DIMENSION IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.75	_	0.80	0.030	_	0.031
A1	0.00	_	0.05	0.000	_	0.002
A2	0.70	0.75	0.78	0.028	0.036	0.031
b	0.35	_	0.50	0.012	_	0.020
С	0.10	_	0.20	0.003	_	0.008
D	2.90 BSC			0.114 BSC		
E	2.80 BSC			0.110 BSC		
E1	1.60 BSC			0.063 BSC		
е	0.95 BSC			0.038 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.37	0.45	0.60	0.012	0.018	0.024
L1	0.60 REF			0	.024 RE	F
L2	0.25 BSC			0	.010 BS	iC
R	0.10	_	_	0.004	_	_
R1	0.10	_	0.25	0.004	_	0.010
θ	0,	4*	8*	0,	4*	8*
θ1	4*	10°	12°	4°	10°	12°
N	6				6	

TSOT-5 Package

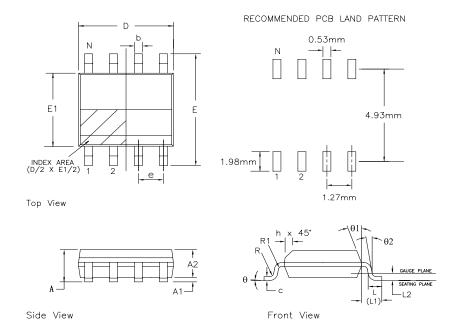


5 Pin TSOT (OPTION 2)						
SYMBOLS	DIMENSION IN MM (Control Unit)			DIMENSION IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.75	_	0.80	0.030	_	0.031
A1	0.00	_	0.05	0.000	_	0.002
A2	0.70	0.75	0.78	0.028	0.030	0.031
b	0.35	_	0.50	0.012	_	0.020
С	0.10	_	0.20	0.003	_	0.008
D	2.90 BSC			0.114 BSC		
E	2.80 BSC			0.110 BSC		
E1	1.60 BSC			0.063 BSC		
е	0.95 BSC			0.038 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.37	0.45	0.60	0.012	0.018	0.024
L1	0.60 REF			0	.024 RE	F
L2	0.25 BSC			0.010 BSC		iC .
R	0.10	_	_	0.004	_	_
R1	0.10	_	0.25	0.004	_	0.010
θ	0,	4*	8,	0,	4.	8*
θ1	4.	10°	12*	4.	10°	12*
N	5				5	

MSOP-8 Package



SOIC-8 Package



8 Pin	SOICN	JEDE	EC MS-	-012	Variatio	n AA	
DIMENSIONS SYMBOLS (Control L				DIMENSIONS IN INCH (Reference Unit)			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.35	_	1.75	0.053	_	0.069	
A1	0.10	_	0.25	0.004	_	0.010	
A2	1.25	_	1.65	0.049	_	0.065	
b	0.31	_	0.51	0.012	_	0.020	
С	0.17	_	0.25	0.007	_	0.010	
E		6.00 BSC			0.236 BSC		
E1	3.90 BSC			0.154 BSC			
е		1.27 BSC		0.050 BSC			
h	0.25	_	0.50	0.010	_	0.020	
L	0.40	_	1.27	0.016	_	0.050	
L1	1.04 REF			0.041 REF			
L2	0.25 BSC			0.010 BSC			
R	0.07	_	_	0.003	_	_	
R1	0.07	_	_	0.003	_	_	
θ	0,	_	8*	0,	_	8*	
θ1	5°	_	15°	5°	_	15°	
θ2	0, —		_	0. —		_	
D	4.90 BSC			0.193 BSC		0	
N	8				8		

Ordering Information

Part Number	Package Green Operating Temperature Rang		Operating Temperature Range	e Packaging	
CLC1005 Ordering Information					
CLC1005IST5X	TSOT-5	Yes	-40°C to +85°C	Tape & Reel	
CLC1005IST5MTR	TSOT-5	Yes	-40°C to +85°C	Mini Tape & Reel	
CLC1005IST5EVB	Evaluation Board	N/A	N/A	N/A	
CLC1005ISO8X	SOIC-8	Yes	-40°C to +85°C	Tape & Reel	
CLC1005ISO8MTR	SOIC-8	Yes	-40°C to +85°C	Mini Tape & Reel	
CLC1005ISO8EVB	Evaluation Board	N/A	N/A	N/A	
CLC1015 Ordering Information					
CLC1015IST6X	TSOT-6	Yes	-40°C to +85°C	Tape & Reel	
CLC1015IST6MTR	TSOT-6	Yes	-40°C to +85°C	Mini Tape & Reel	
CLC1015IST6EVB	Evaluation Board	N/A	N/A	N/A	
CLC2005 Ordering Information					
CLC2005ISO8X*	SOIC-8	Yes	-40°C to +85°C	Tape & Reel	
CLC2005ISO8MTR*	SOIC-8	Yes	-40°C to +85°C	Mini Tape & Reel	
CLC2005ISO8EVB*	Evaluation Board	N/A	N/A	N/A	
CLC2005IMP8X*	MSOP-8	Yes	-40°C to +85°C	Tape & Reel	
CLC2005IMP8MTR*	MSOP-8	Yes	-40°C to +85°C	Mini Tape & Reel	
CLC2005IMP8EVB*	Evaluation Board	N/A	N/A	N/A	

Moisture sensitivity level for all parts is MSL-1. Mini tape and reel quantity is 250.

Revision History

Revision	Date	Description
2D (ECN 1513-01)	March 2015	Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Updated thermal resistance numbers and package outline drawings. Added CLC1015 back into data sheet.
2D.R	July 2018	Updated to Resurgent Semiconductor.

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